

Achieving broadband near-infrared emission with superior anti-thermal quenching by optimizing excited-state population of Cr³⁺ in Gd₃ScGa₄O₁₂ garnet phosphors

Wangyu Liu^a, Lifang Yuan^b, Haoyi Wu^a, Huafeng Dong^a, Yahong Jin^{*ac}

^aSchool of Physics and Optoelectronic Engineering, Guangdong University of Technology, WaiHuan Xi Road, No. 100, Guangzhou 510006, China.

^bSchool of Electronics and Communications, Guangdong Mechanical & Electrical Polytechnic, Guangzhou 510515, China

^cGuangdong Provincial Key Laboratory of Sensing Physics and System Integration Applications, WaiHuan Xi Road, No. 100, Guangzhou 510006, China.

E-mail: yhj@gdut.edu.cn

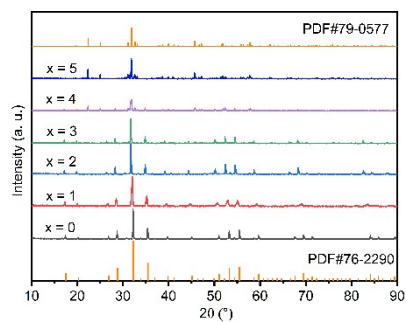


Fig. S1. XRD patterns of $\text{Gd}_3\text{Sc}_x\text{Ga}_{5-x}\text{O}_{12}:0.08\text{Cr}^{3+}$ ($x = 0-5$).

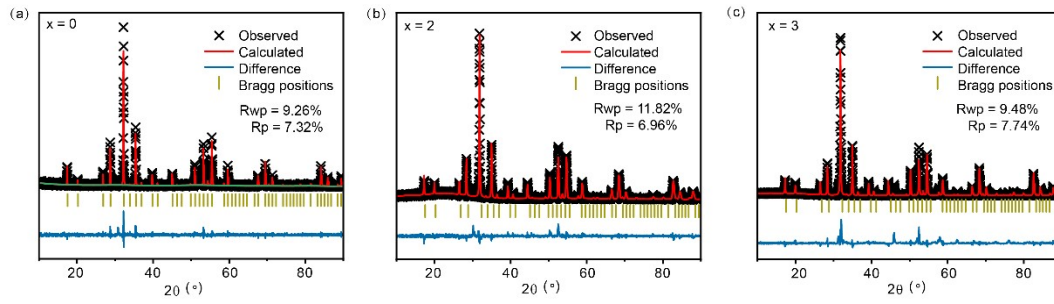


Fig. S2. (a–c) XRD Rietveld refinement of $\text{Gd}_3\text{Sc}_x\text{Ga}_{5-x}\text{O}_{12}$ ($x = 0, 2, 3$).

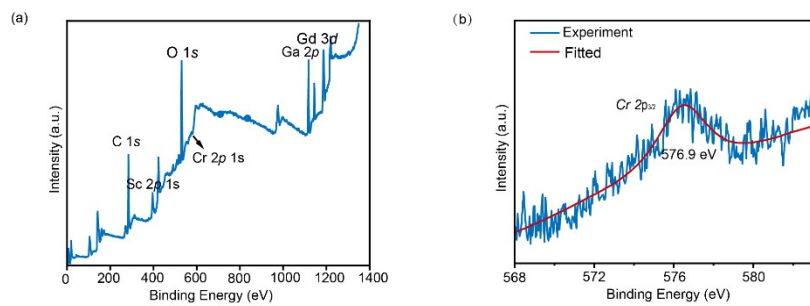


Fig. S3. (a) XPS full spectrum and (b) Cr 2p scan of $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$.

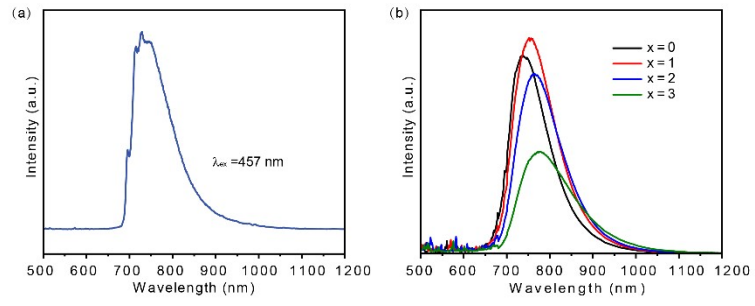


Fig. S4. (a) Emission spectrum of $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$ at 77 K. (b) Relative emission intensity of $\text{Gd}_3\text{Sc}_x\text{Ga}_{5-x}\text{O}_{12}:0.08\text{Cr}^{3+}$ ($x = 0-3$).

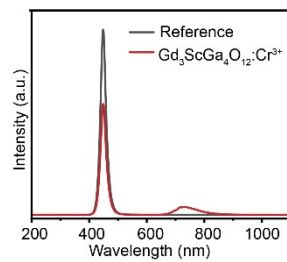


Fig. S5. IQE (82.75%), EQE (28.19%), and absorption coefficient (34.07%) of $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$.

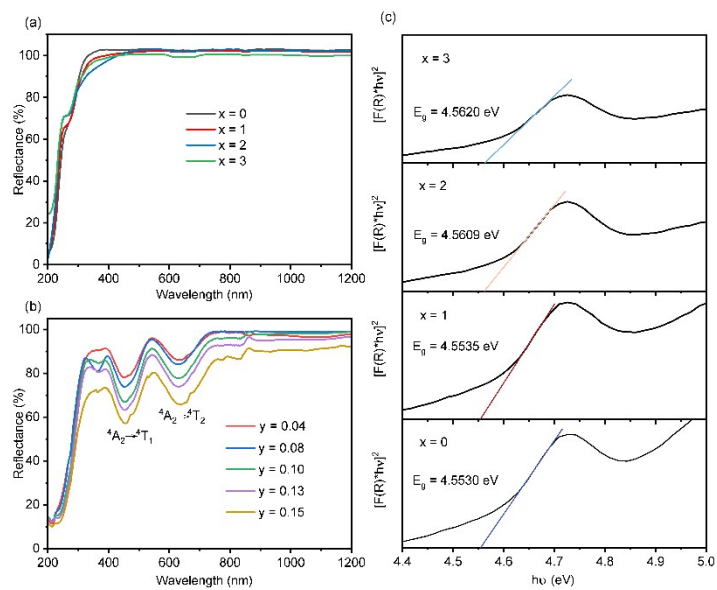


Fig. S6. (a) DRS of $Gd_3Sc_xGa_{5-x}O_{12}$ ($x = 0-3$). (b) DRS of $Gd_3ScGa_4O_{12}:yCr^{3+}$ ($y = 0.04-0.15$). (c) The estimated optical band gaps of $Gd_3Sc_xGa_{5-x}O_{12}$ ($x = 0-3$).

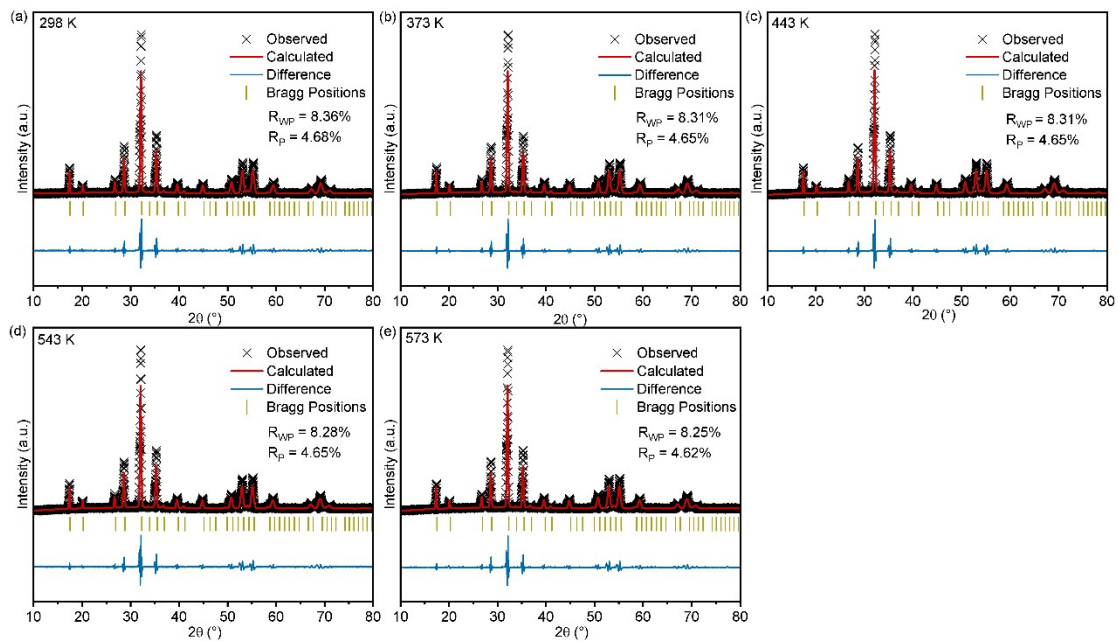


Fig. S7. XRD Rietveld refinement of (a) $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$ at (a) 25 °C, (b) 100 °C, (c) 170 °C, (d) 270 °C, (e) 300 °C.

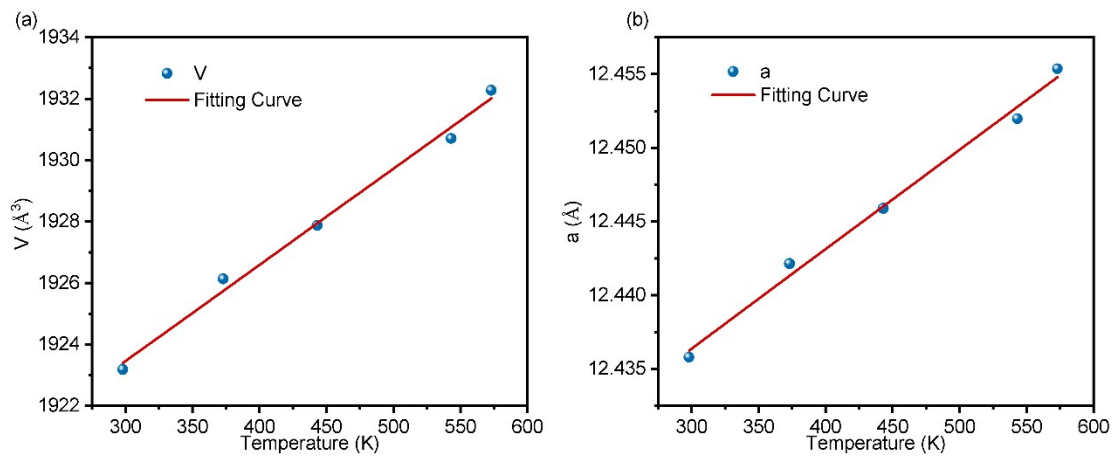


Fig. S8. Temperature-dependent (a) volume and (b) lattice parameters for $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$.

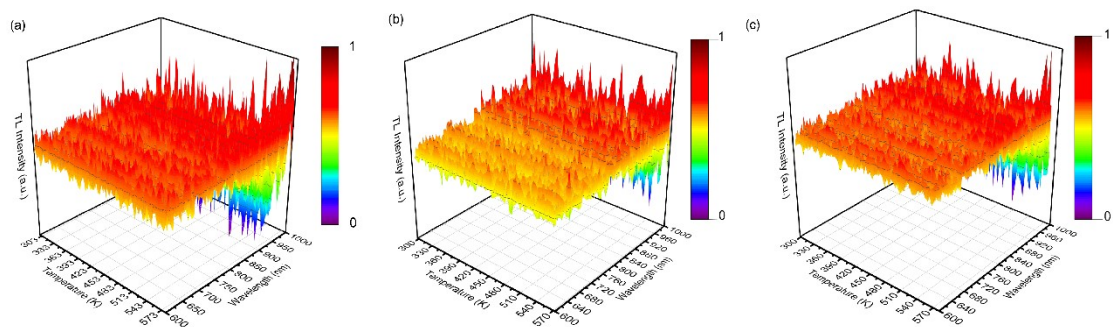


Fig. S9. Thermoluminescence curves of $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$ measured without preheating (a) and with preheating at (b) 100 °C and (c) 150 °C under 460 nm excitation.

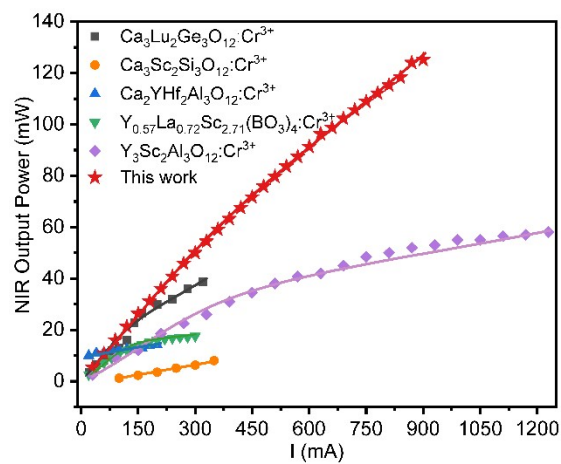


Fig. S10. A comparison of the NIR output power with other garnet NIR phosphors reported previously.^[1-5]

Table S1. Crystallographic data of $\text{Gd}_3\text{Sc}_x\text{Ga}_{5-x}\text{O}_{12}$ ($x = 0-3$).

Samples	x = 0	x = 1	x = 2	x = 3
Crystal system		Cubic		
Space group		$\text{Ia}\bar{3}\text{d}$		
a=b=c (Å)	12.3691	12.4523	12.5496	12.5747
$\alpha=\beta=\gamma$	90	90	90	90
Volume (Å ³)	1892.389	1930.835	1976.485	1988.344
Sc-O ₆ (Å)	1.999	2.012	2.076	2.087
R _p	0.0732	0.0731	0.0696	0.0774
R _{wp}	0.0926	0.0936	0.1182	0.0948
χ^2	1.35	1.299	1.827	4.937
Gd1	(0.125,0.000,0.250)	(0.125,0.000,0.250)	(0.125,0.000,0.250)	(0.125,0.000,0.250)
Ga1	(0.000,0.000,0.000)	(0.000,0.000,0.000)	(0.000,0.000,0.000)	(0.000,0.000,0.000)
Ga2	(0.375,0.000,0.250)	(0.375,0.000,0.250)	(0.375,0.000,0.250)	(0.375,0.000,0.250)
O1	(0.967,0.053,0.149)	(0.968,0.052,0.150)	(0.968,0.053,0.150)	(0.969,0.053,0.151)
Sc1	(0.000,0.000,0.000)	(0.000,0.000,0.000)	(0.000,0.000,0.000)	(0.000,0.000,0.000)

Table S2. The survey of ion-doped (excluding Cr³⁺-doped) inorganic phosphors with anti-TQ performance.

Host materials	Activators	Ex/Em (nm)	FWHM (nm)	IQE	I _T /I _{RT}	Ref.
Ba ₂ ZnGe ₂ O ₇	Bi ³⁺	346/500	129	–	138%@423K	[6]
Na ₃ Ca ₄ TeP ₃ O ₁₅	Tb ³⁺ , Eu ³⁺	376/545, 617		–	109%@423K	[7]
Lu ₂ SrAl ₄ SiO ₁₂	Eu ²⁺	342/420		–	106%@423K	[8]
Sc _{1.8} Zr _{0.1} Nb _{0.1} W _{2.85} O _{11.7}	Yb/Er ³⁺	522/980		–	114%@448K	[9]
Ca _{3.6} In _{3.6} (PO ₄) ₆	Dy ³⁺	349/575		30.3%	108.2%@423K	[10]
Ba ₃ EuAl ₂ O _{7.5}	Eu ³⁺	270/593			140%@443K	[11]
Ca ₂ InSbO ₆	Eu ³⁺	395/616		82%	114.5%@380K	[12]
LaSc ₃ (BO ₃) ₄	Eu ³⁺	395/618		88.3%	129.2%@548K	[13]
KAl ₁₁ O ₁₇	Mn ²⁺	450/510	~50	–	160%@548K	[14]
Cs ₂ MP ₂ O ₇ (M=Ba,Sr,Ca)	Eu ²⁺	360/548		98.9%	120%@448K	[15]
Mg ₃ Y ₂ Ge ₃ O ₁₂	Eu ³⁺ , Mn ⁴⁺	420/660		–	127%@500K	[16]
CsMoO ₂ F ₃	Mn ⁴⁺	450/633		54%	129.3%@423K	[17]
LaAlO ₃	Ca ²⁺ , Bi ³⁺ , Mn ⁴⁺	340/734		89.3%	103%@423K	[18]
In _{0.5} Sc _{1.5} (MoO ₄) ₃	Eu ³⁺	246/615		57.8%	108.2%@473K	[19]

Table S3. Crystallographic data of $\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$ at different temperatures.

Materials	$\text{Gd}_3\text{ScGa}_4\text{O}_{12}:0.08\text{Cr}^{3+}$				
Measuring temperature/ $^{\circ}\text{C}$	25	100	170	270	300
Crystal system			Cubic		
Space group			$\text{Ia}\bar{3}\text{d}$		
a=b=c (\AA)	12.4440	12.4498	12.4563	12.4652	12.4687
$\alpha=\beta=\gamma$	90°	90°	90°	90°	90°
Volume (\AA^3)	1926.995	1929.669	1932.691	1936.864	1938.468
Average bond length of Cr-O (\AA)	2.053	2.055	2.057	2.058	2.061
Volume of CrO_6 octahedron (\AA^3)	11.4548	11.4942	11.5276	11.5486	11.6141
R_p	0.0469	0.0466	0.0466	0.0466	0.0464
R_{wp}	0.0838	0.0832	0.0833	0.0829	0.0827
χ^2	2.08	2.86	2.92	2.79	2.67

References:

- [1] J. Feng, X. Wu, D. Zhu, J. Chen, Z. Mu, *Journal of Luminescence* **2022**, 252, 119379.
- [2] Y. Zhou, X. Li, T. Seto, Y. Wang, *ACS Sustainable Chemistry & Engineering* **2021**, 9, 3145-3156.
- [3] D. Huang, Q. Ouyang, H. Xiao, B. Wang, H. Lian, Q. Zeng, J. Lin, *Dalton Transactions* **2021**, 51, 908-916.
- [4] D. Qian, Y. Jin, Y. Li, H. Wu, Y. Hu, *Applied Physics A* **2024**, 130, 233.
- [5] H. Wu, L. Jiang, K. Li, C. Li, H. Zhang, *Journal of Materials Chemistry C* **2021**, 9, 11761-11771.
- [6] Y. Wei, H. Yang, Z. Gao, X. Yun, G. Xing, C. Zhou, G. Li, *Laser & Photonics Reviews* **2021**, 15, 2000048.
- [7] R. Song, R. Wang, X. Yang, X. Bian, H. Fu, *Applied Materials Today* **2024**, 38, 102246.
- [8] T. Ying-Ying, Y. Zi-Han, W. Chun-Hao, W. Ting-Wei, L. Fa-Chun, *Journal of the American Ceramic Society* **2022**, 105, 5240.
- [9] B. Fu, H. Yan, R. Li, L. Feng, Y. Yu, G. Gong, H. Huang, J. Liao, *Laser & Photonics Reviews* 2400739, doi.org/10.1002/lpor.202400739.
- [10] R.-R. Wang, J. Zhang, Y.-J. Liu, G.-H. Li, G.-M. Cai, *Dalton Transactions* **2023**, 52, 5552.
- [11] X. Bian, R. Wang, S. Li, Q. Shi, H. Fu, *Journal of Luminescence* **2023**, 257, 119768.
- [12] X. Geng, Y. Xie, Y. Ma, Y. Liu, J. Luo, J. Wang, R. Yu, B. Deng, W. Zhou, *Journal of Alloys and Compounds* **2020**, 847, 156249.
- [13] S. Wang, Y. Xu, T. Chen, W. Jiang, J. Liu, X. Zhang, W. Jiang, L. Wang, *Chemical Engineering Journal* **2021**, 404, 125912.
- [14] Z. Zhou, H. Zhu, X. Huang, Y. She, Y. Zhong, J. Wang, M. Liu, W. Li, M. Xia, *Chemical Engineering Journal* **2022**, 433, 134079.
- [15] Y. Wei, Z. Gao, S. Liu, S. Chen, G. Xing, W. Wang, P. Dang, A. A. Al Kheraif, G. Li, J. Lin, *Advanced Optical Materials* **2020**, 8, 1901859.
- [16] Y. Wei, H. Yang, Z. Gao, Y. Liu, G. Xing, P. Dang, A. A. A. Kheraif, G. Li, J. Lin, R. S. Liu, *Advanced Science* **2020**, 7, 1903060.
- [17] S. He, F. Xu, T. Han, Z. Lu, W. Wang, J. Peng, F. Du, F. Yang, X. Ye, *Chemical Engineering Journal* **2020**, 392, 123657.
- [18] S. Fang, T. Lang, T. Han, J. Wang, J. Yang, S. Cao, L. Peng, B. Liu, A. N. Yakovlev, V. I. Korepanov, *Chemical Engineering Journal* **2020**, 389, 124297.
- [19] T. Tian, Z. Wang, C. Mao, M. Chen, Y. Chu, Y. Li, *Journal of Alloys and Compounds* **2024**, 973, 172887.